Bonding and CMP

Victor Ovchinnikov

Chapters 16, 17

Previous lecture

- Doping:
  - diffusion
  - ion implantation
- Epitaxy

- Integration

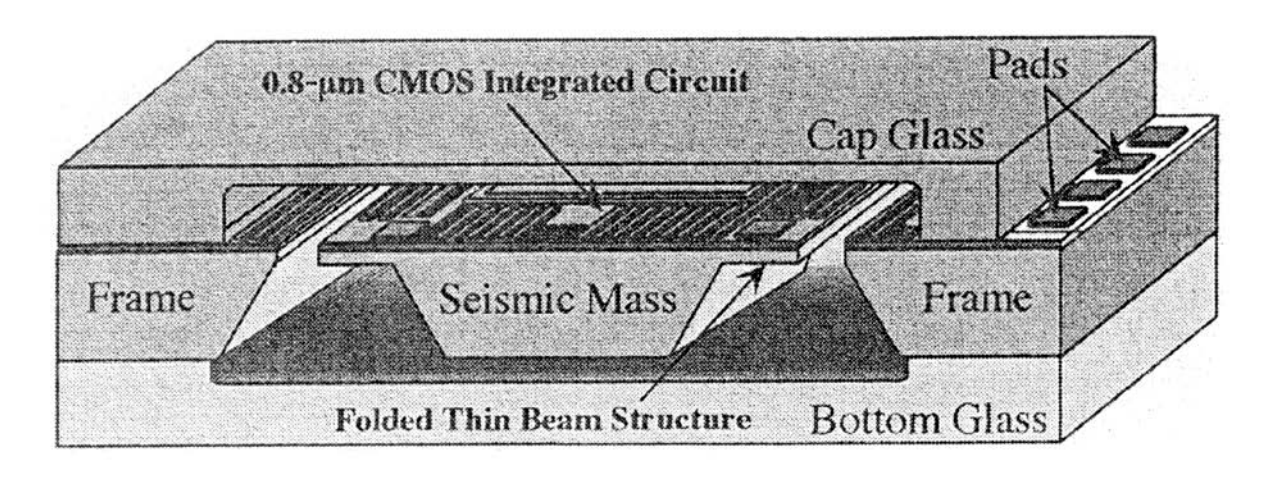
Outlook

- Bonding mechanics
- Bonding techniques
- CMP
- Etching vs. CMP

Accelerometer (glass-Si-glass)

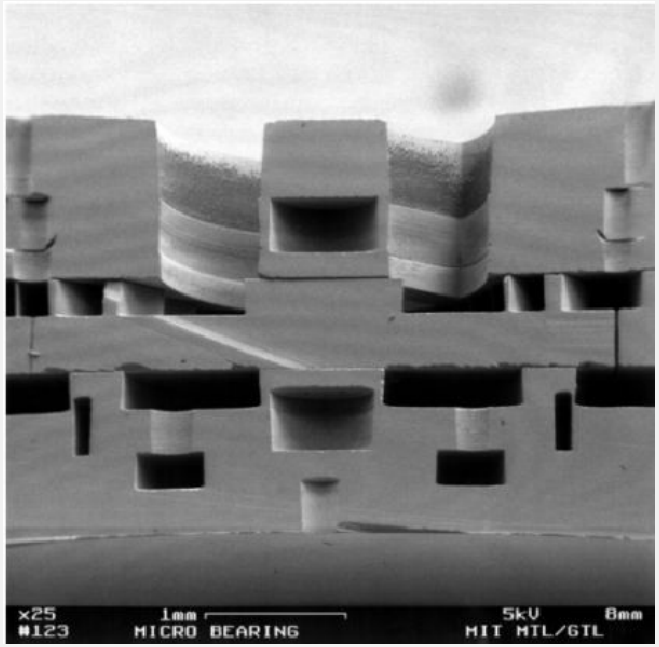
Anodic bonding: silicon-to-glass. Twice

Hermetic cavity (vacuum)



Wafer bonding applications

- Advanced substrates (SOI)
- Packaging
- Capping/Encapsulation
- Multi layer devices
- 3D structures
- Layer transfer



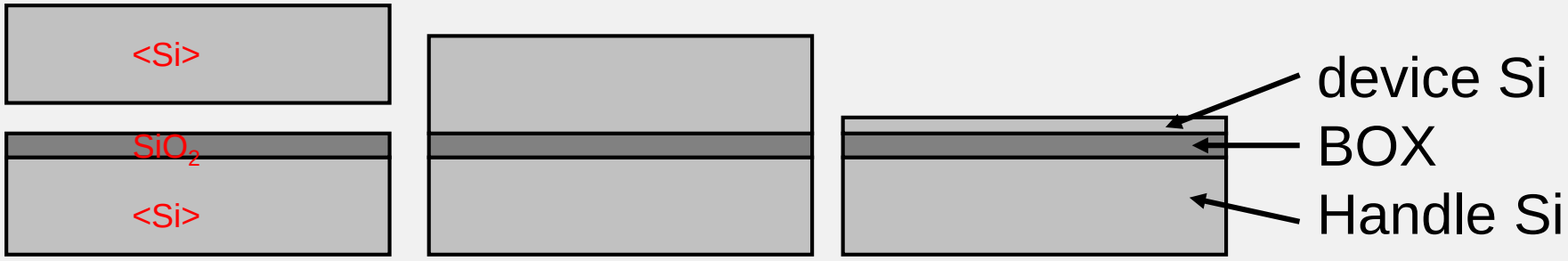
5 wafers, 380 µm each
No wafer thinning
Bonding – one at a time

Wire bonding
Flip chip bonding

} Not part of this course

SOI wafer fabrication

Surface preparation **RT joining. Anneal** **Thinning**



BOX= buried oxide

Basic requirements for bonding

Wafers are flat (no centimeter scale wavyness)

Wafers are smooth (atomic/micrometer scale)

Materials form chemical bonds across the interface

No high stress

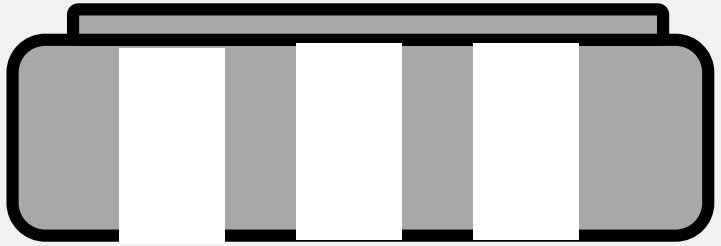
No interface bubbles

Why SOI wafers ?

CMOS

-easy isolation of transistors
-fewer process steps
-elimination of substrate effects
➔ faster transistors

MEMS



-easy etch stop
-single crystal material superior
-device and handle silicon optimized separately

Why not SOI ? Expensive

Bonding process steps

-particle removal

-surface chemistry modification

-(optional) vacuum pumping

-(optional) wafer alignment

-room temperature joining

-application of force/heat/voltage

-(optional) wafer thinning

Bonding techniques

- silicon direct bonding (SDB) = fusion bonding (FB):
  (Si/Si or SiO_2/Si or SiO_2/SiO_2)
- anodic bonding (AB) = field assisted thermal bonding (FATB):
  Si/glass, glass/Si/glass
- thermo-compression bonding (TCB):
  Au-Au
- eutectic bonding:
  Si/Au (363 ^oC)
- adhesive bonding, “glueing”:
  Si/polymer/silicon
- glass frit bonding:
  glass soldering

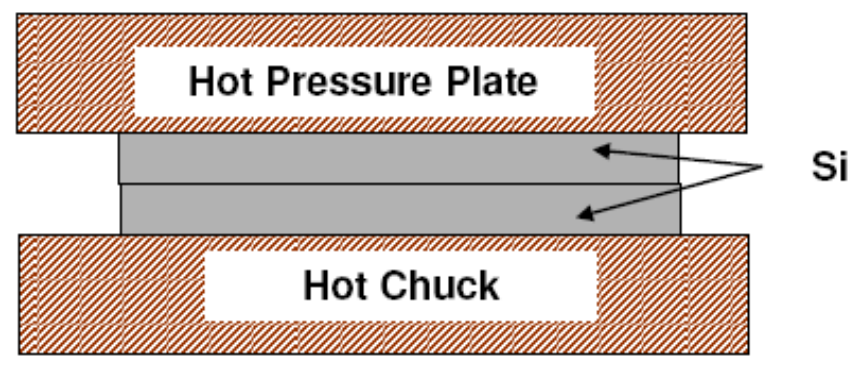
Direct (fusion) bonding

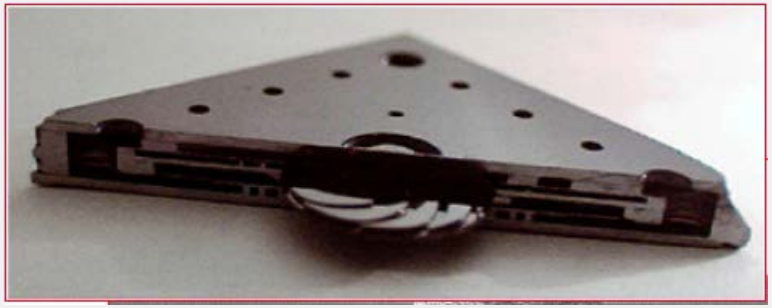
- surface cleaning in RCA-1 (NH_4OH-H_2O_2)
- room temperature joining
- initiation of bonding at centre or wafer flat
- anneal for bond energy improvement
- further processing with some limitations:

  gases in cavities expand

  thin membranes bend

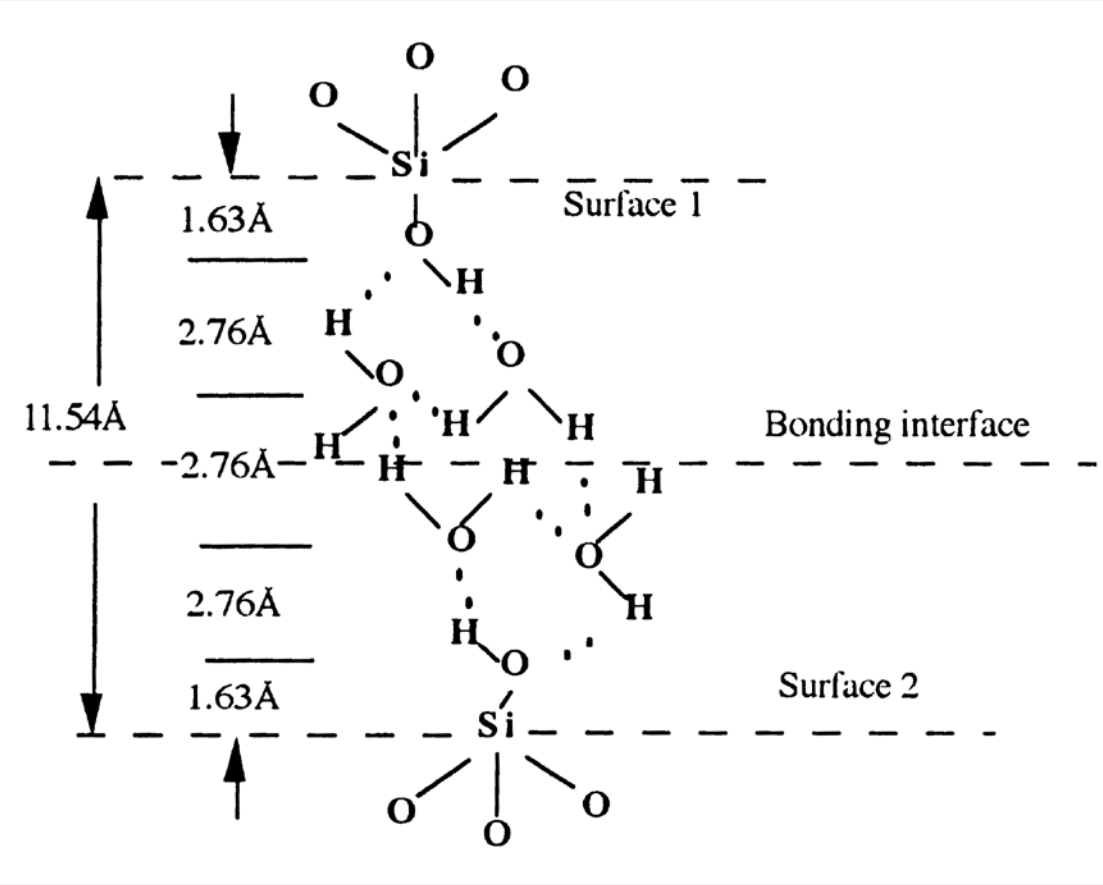
  bonded wafer stack is thicker than usual





M.Schmidt, MIT

Bonding of hydrophylic Si surfaces: low temperature, low strength



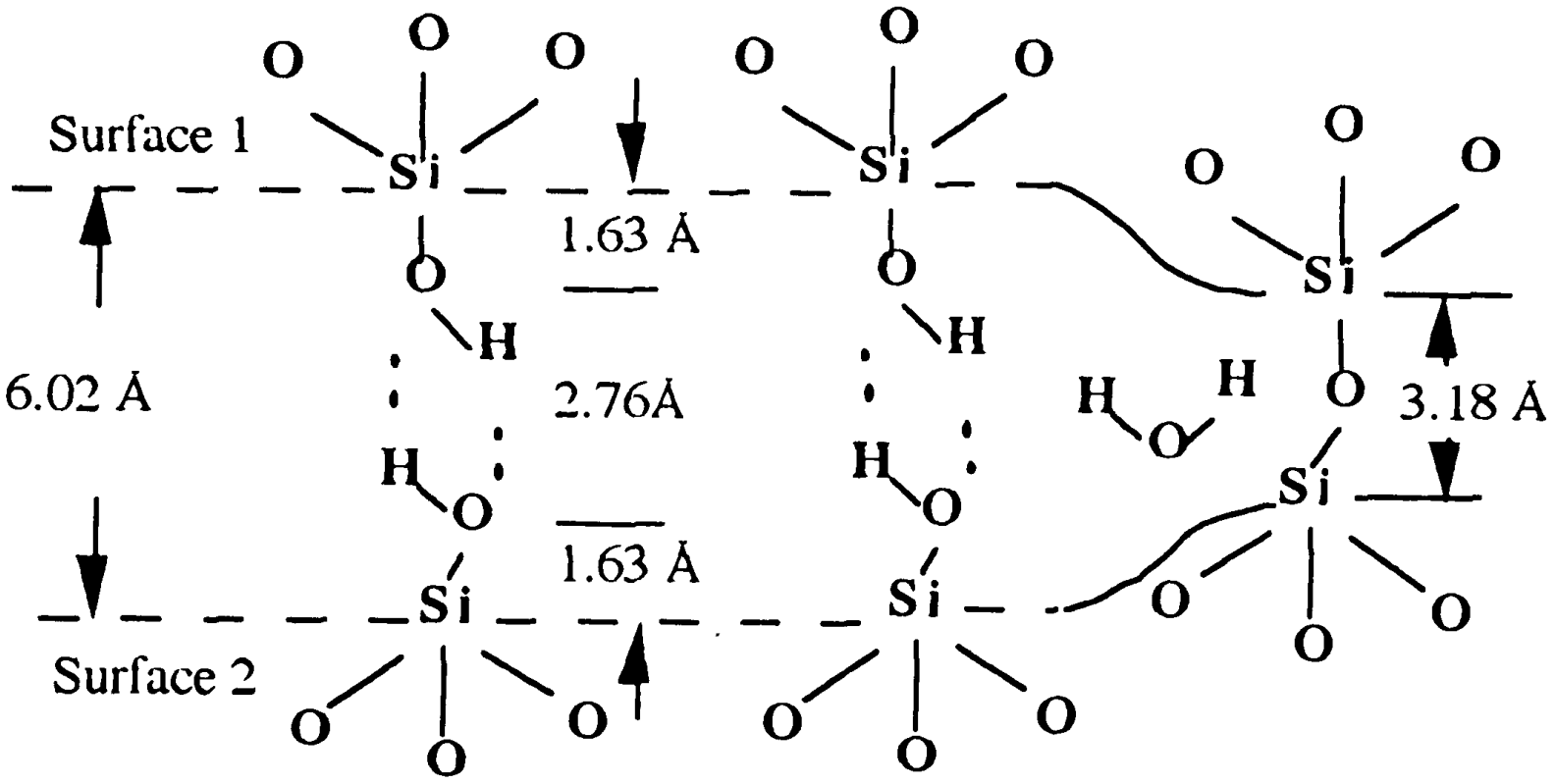
Surface energy

$\gamma = (1/2)\, E_{bond}\, d_{bond}$,

E_{bond} - bond strength
d_{bond} - bond density

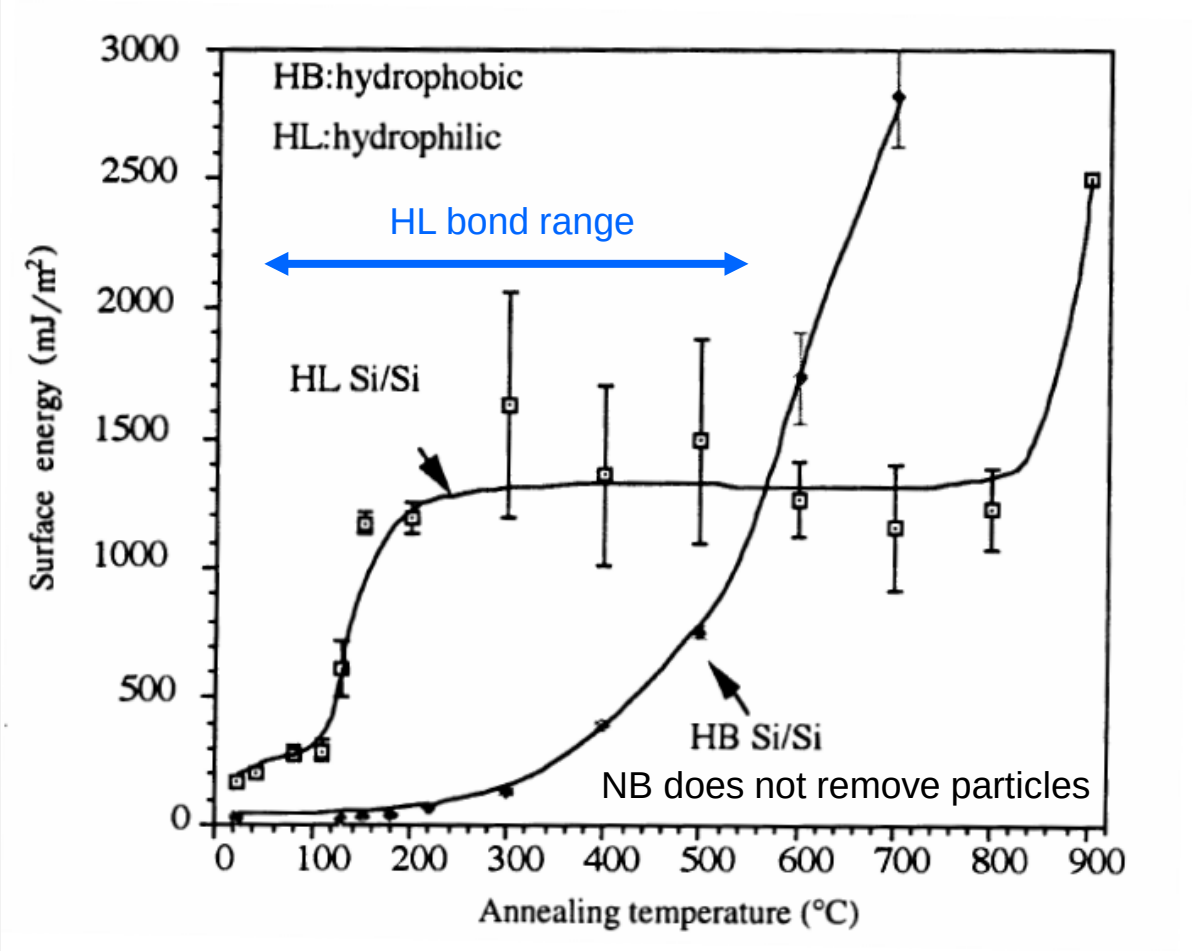
Silanol groups Si-OH
γ = 200 mJ/m^2

H_2O removing and siloxane bond formation: high temperature, high strength



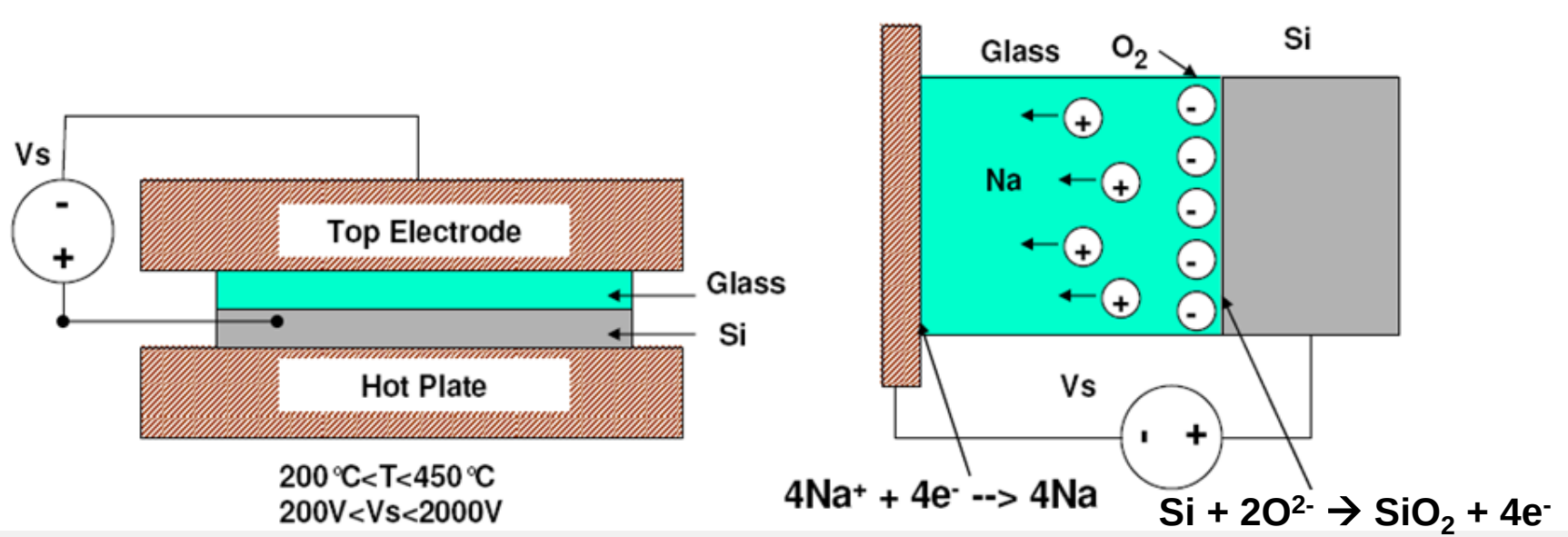
Siloxane groups O-Si-O γ = 1300 mJ/m^2

Bond strength



Tong & Gösele: Semiconductor wafer bonding

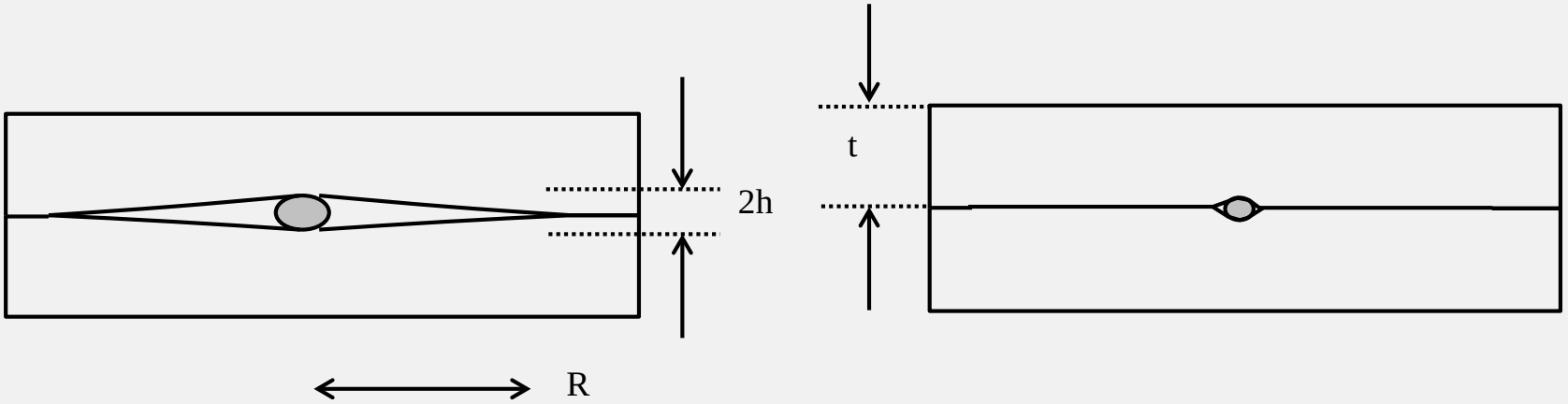
Anodic bonding



1. Limited number of glasses can be used (CTE problem), e.g. Pyrex 7740
2. Surface cleaning to remove particles. Native oxide is not a problem
3. Pump to vacuum, heating, alignment
4. Mechanical contact and applying voltage

Electrostatic force pull wafers together and SiO_2 bonds are created

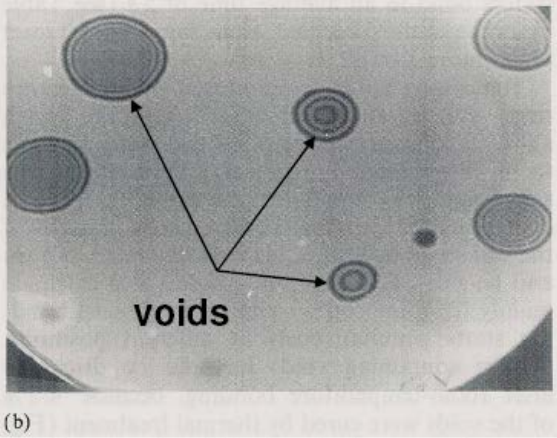
Problems with particles



Voids created by particles are very large compared to particles themselves because silicon is rigid material

Silicon can conform only to very small particles, < 100 nm

Problems with trapped gas

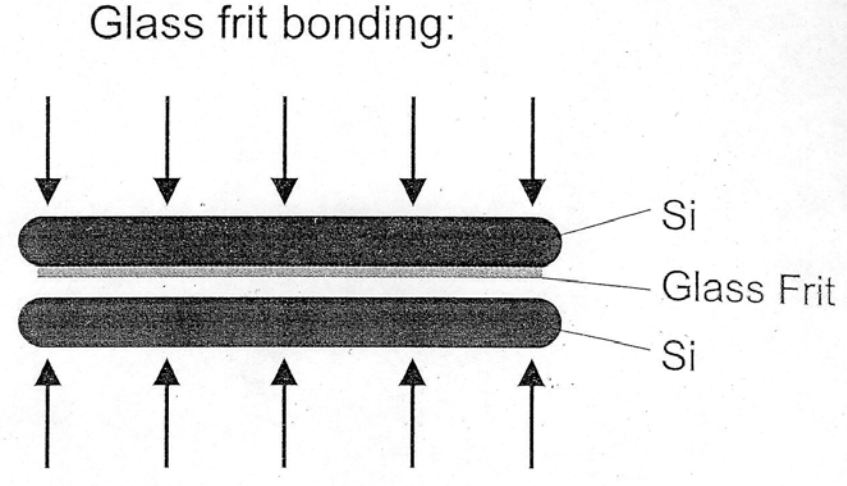


Some of voids due to trapped gas

From Sami Franssila presentation, Microsyste tech., 2006

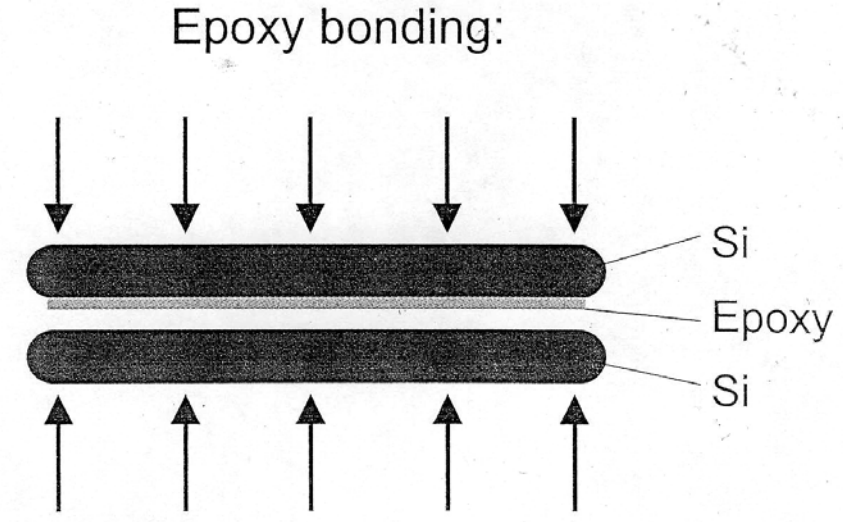
Glass frit and adhesive bonding

Rough surfaces
High strength
No outgassing



500ºC

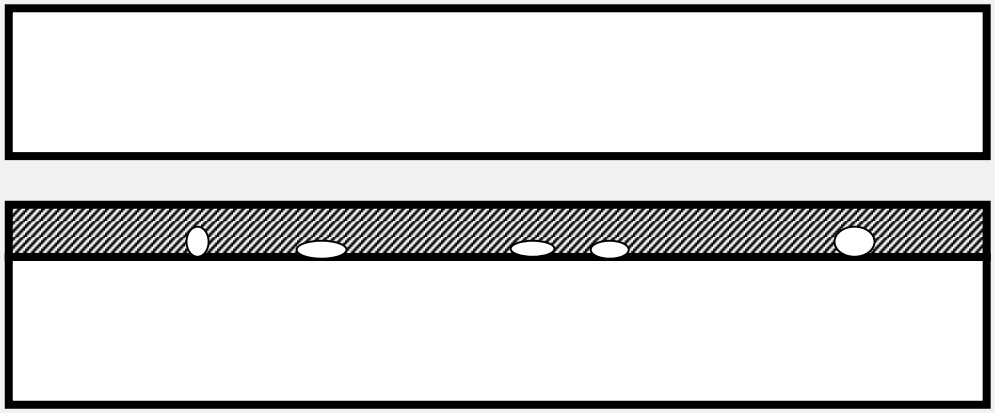
Rough surfaces
Low temperature



100ºC

Adhesive bonding

Deposit adhesive polymer on wafer



Any materials

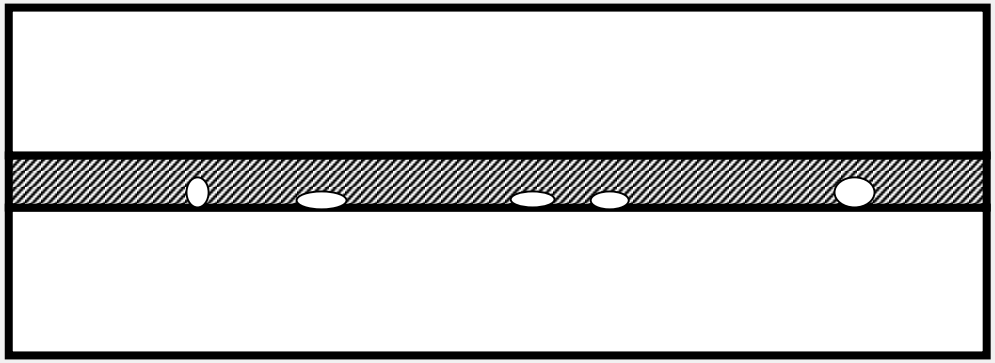
Low temperature <200C

Tolerant to particles

Structured wafers

Low cost

Bring to contact at T>Tg and bake



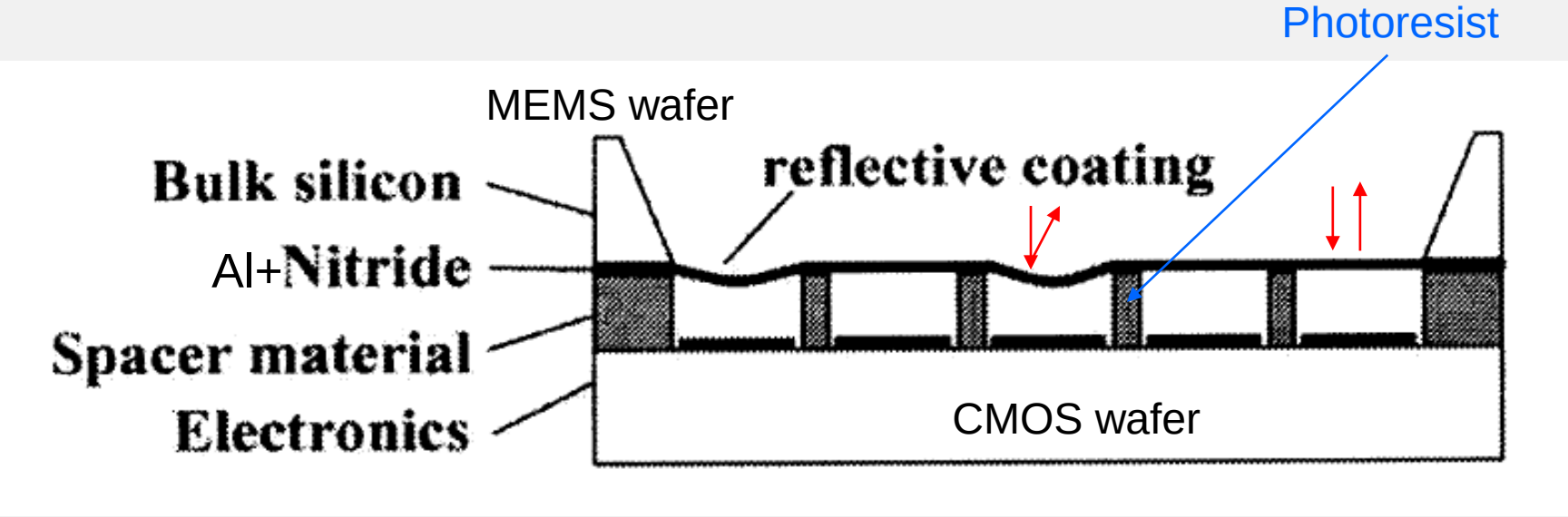
Instability

Outgassing

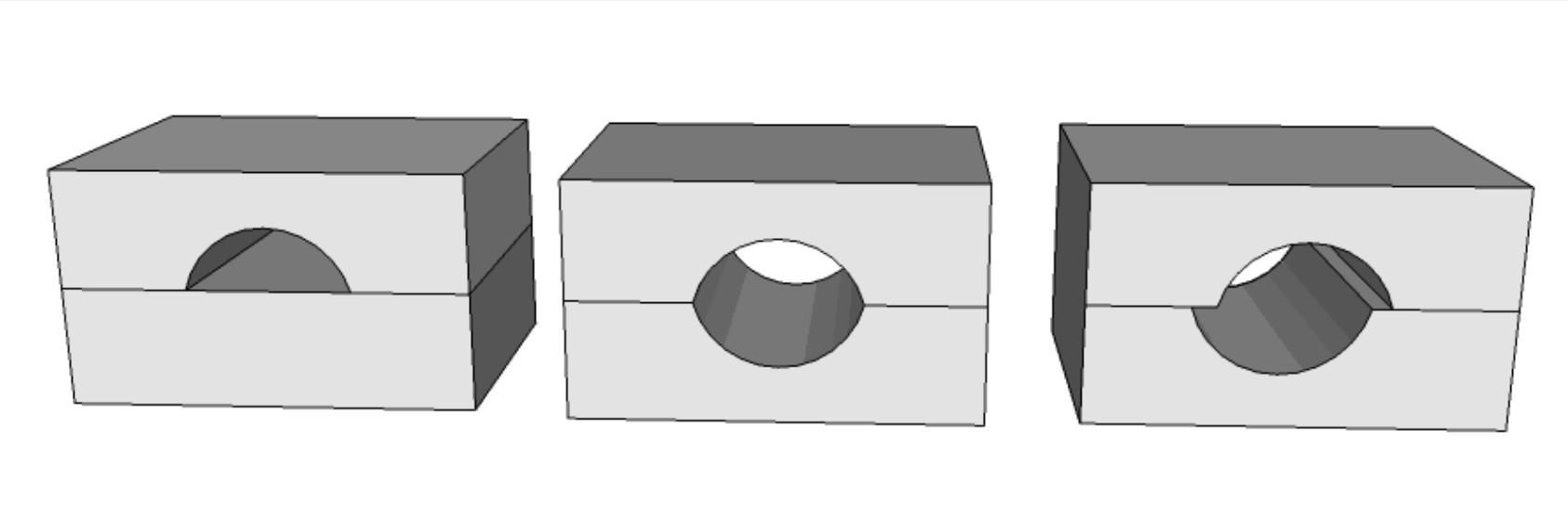
Moisture penetration

Adhesive bonding with pattern

Al mirror on nitride membrane



Bond alignment I



None

Simple equipment enough

Perfect

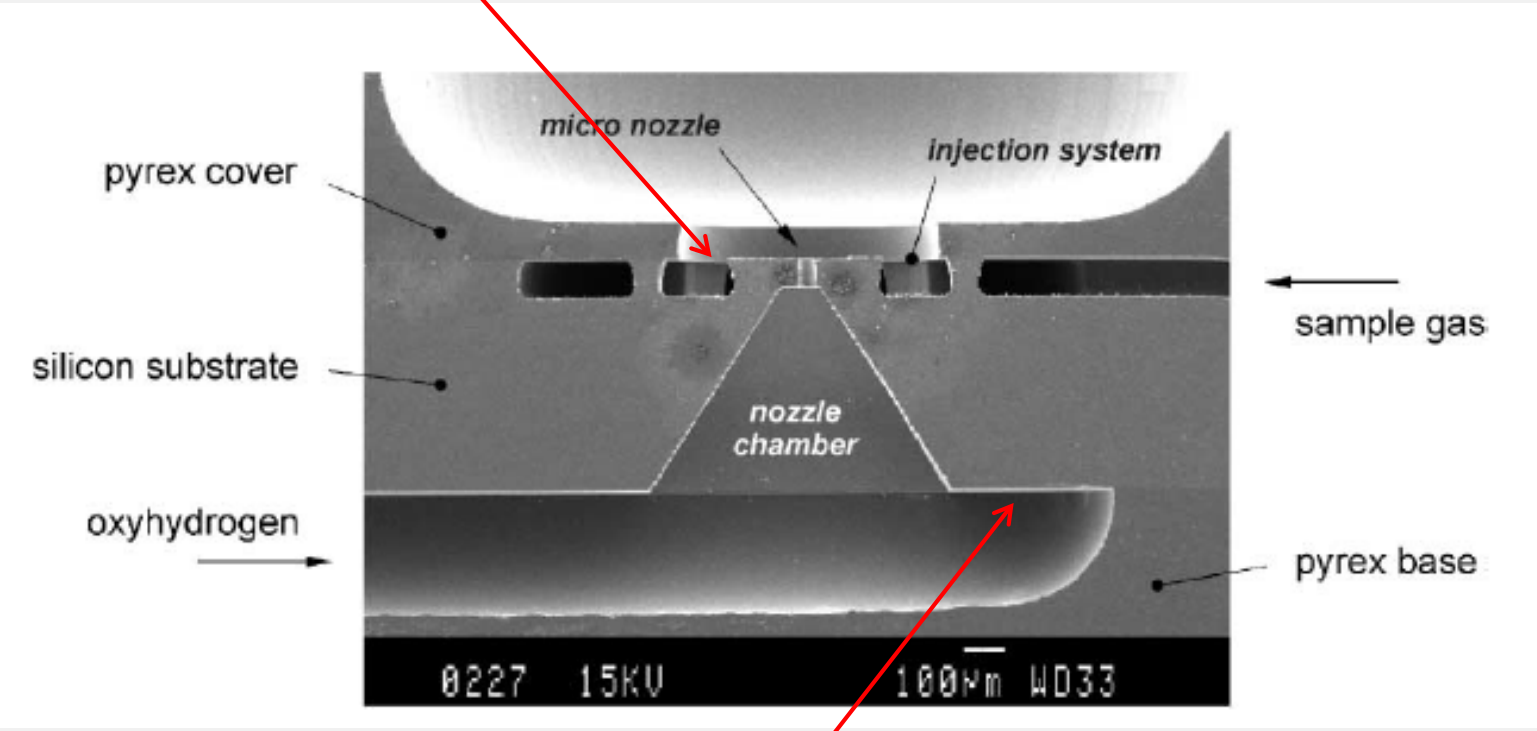
Requires advanced tools

Misaligned

Some devices more sensitive to misalignment than others.

Bond alignment II

Critical alignment



Non-critical alignment

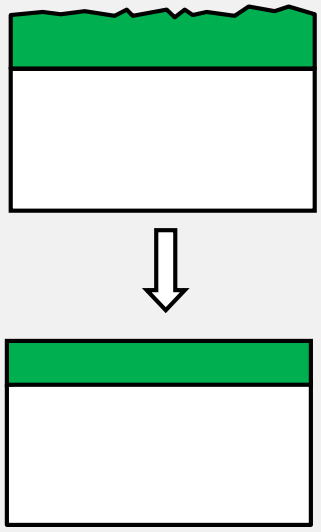
Chemical mechanical planarization

- Chemical Mechanical Planarization (CMP) combines chemical action with mechanical abrasion to achieve selective material removal through polishing

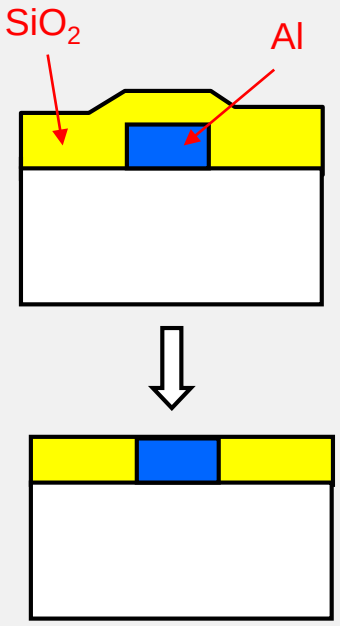
- CMP achieves the greatest degree of planarization of any currently known technique

Applications of polishing

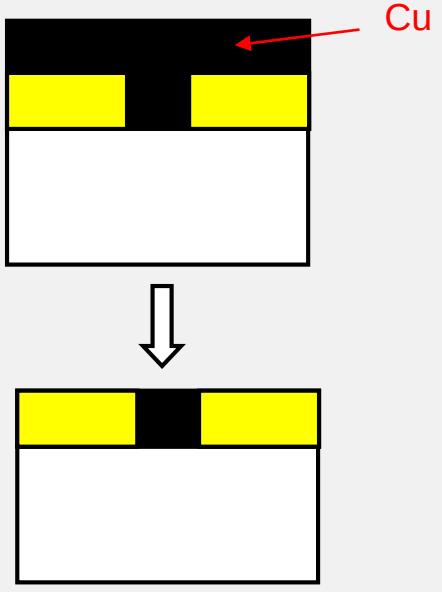
Smoothing



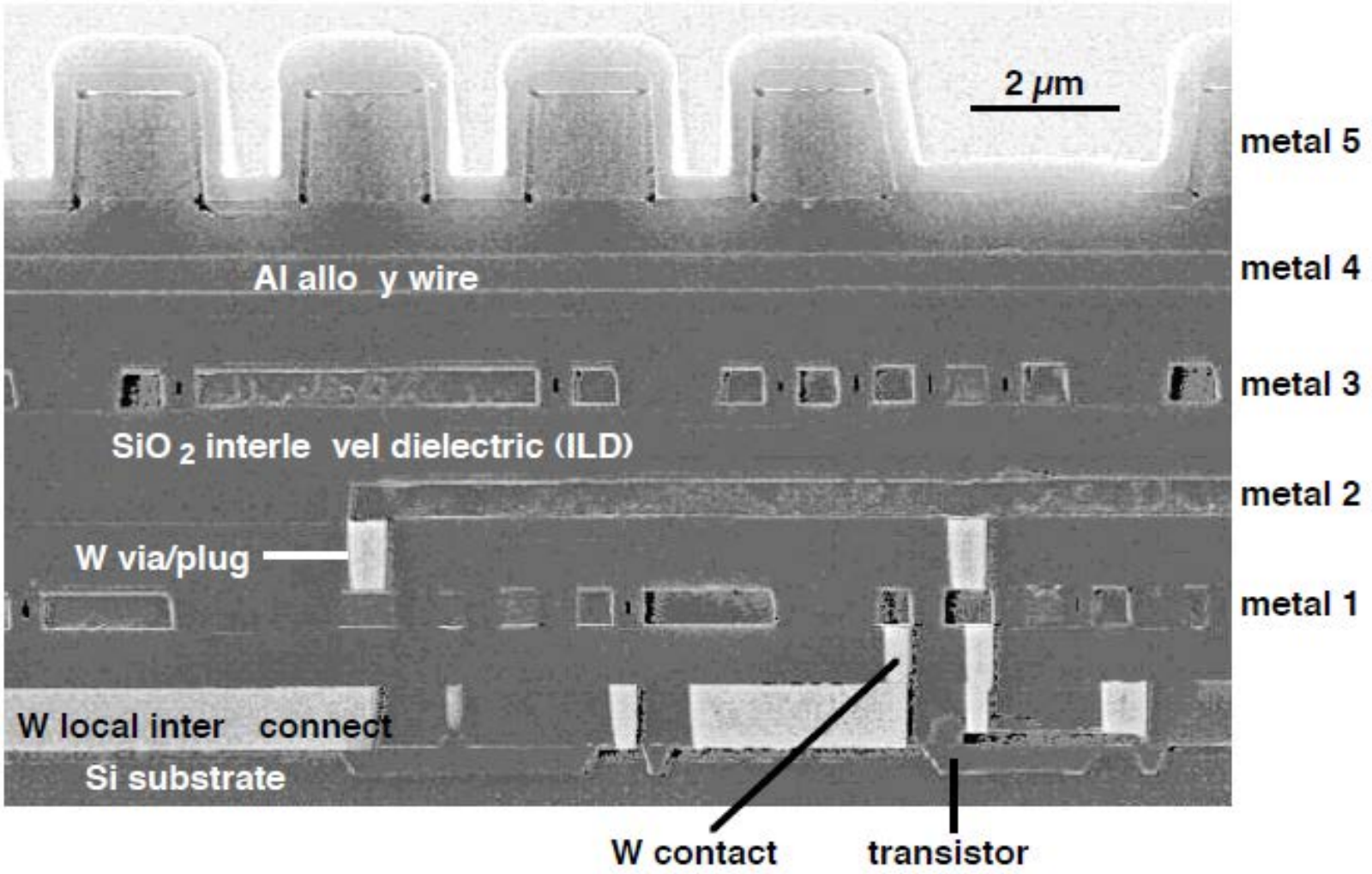
Planarization



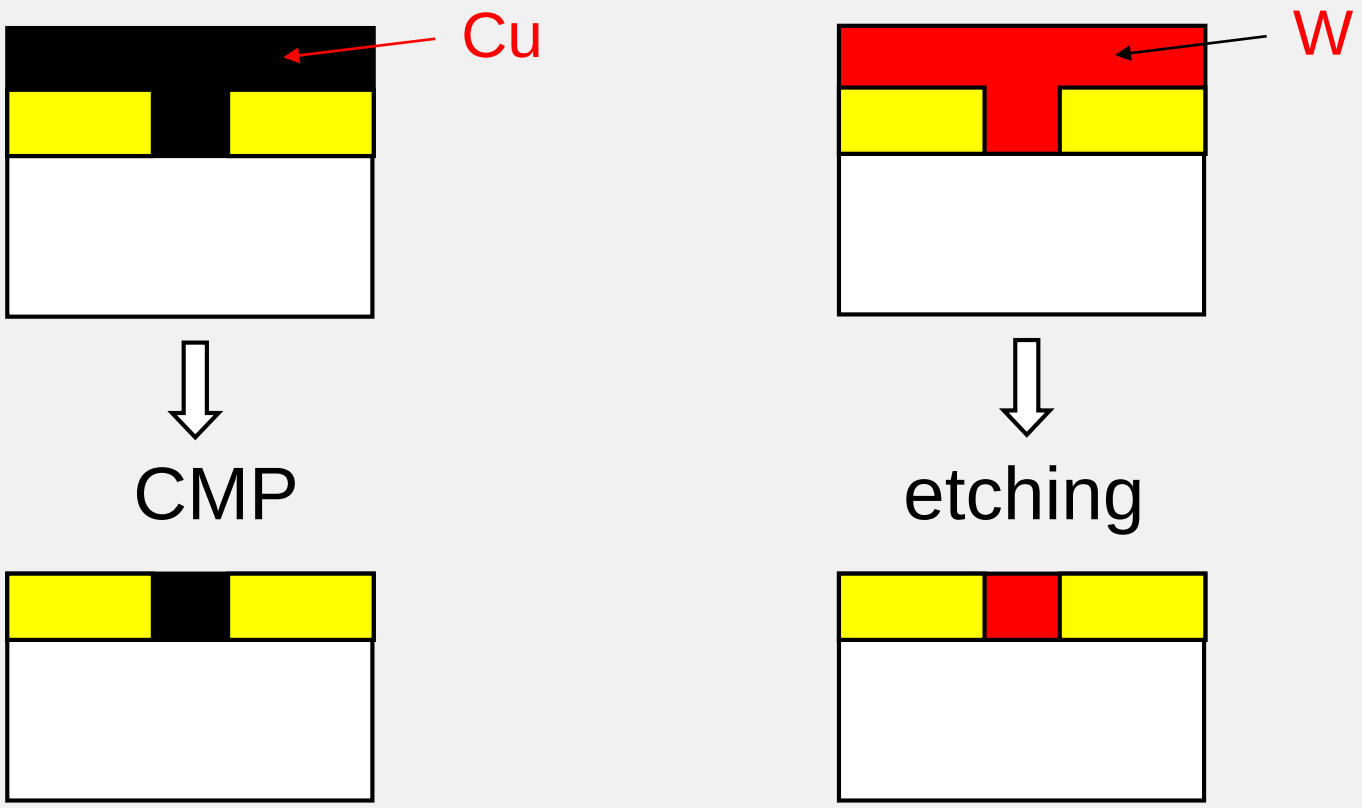
Damascene



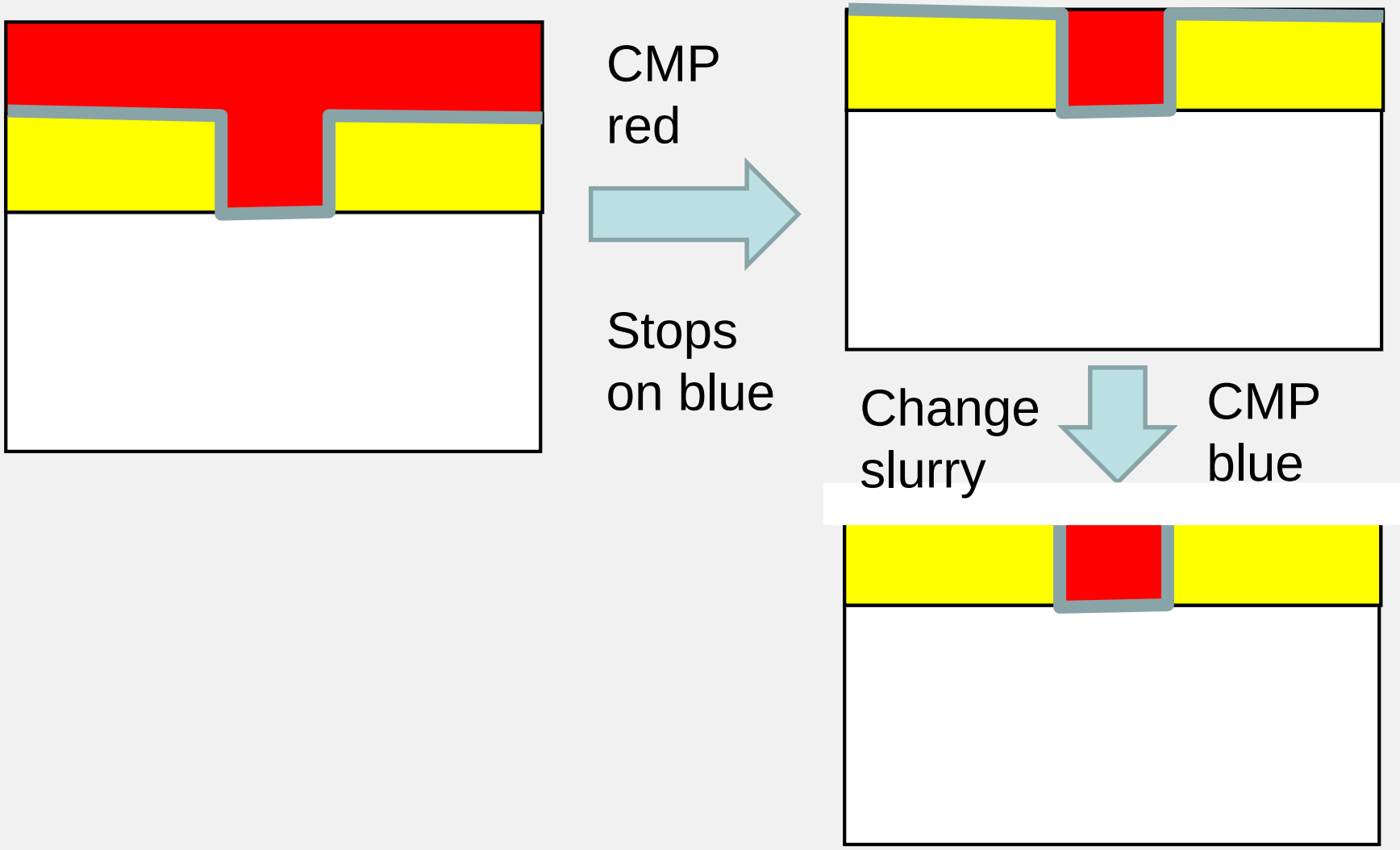
A Motorola μprocessor with 5 Al layers



Cu damascene vs. W etchback ?



Multilayer polishing



Polish selectivity & polish stop

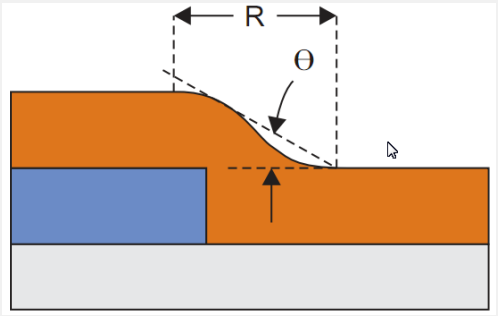
Polish selectivity:

Polishing rate of material 1/polishing rate of material 2

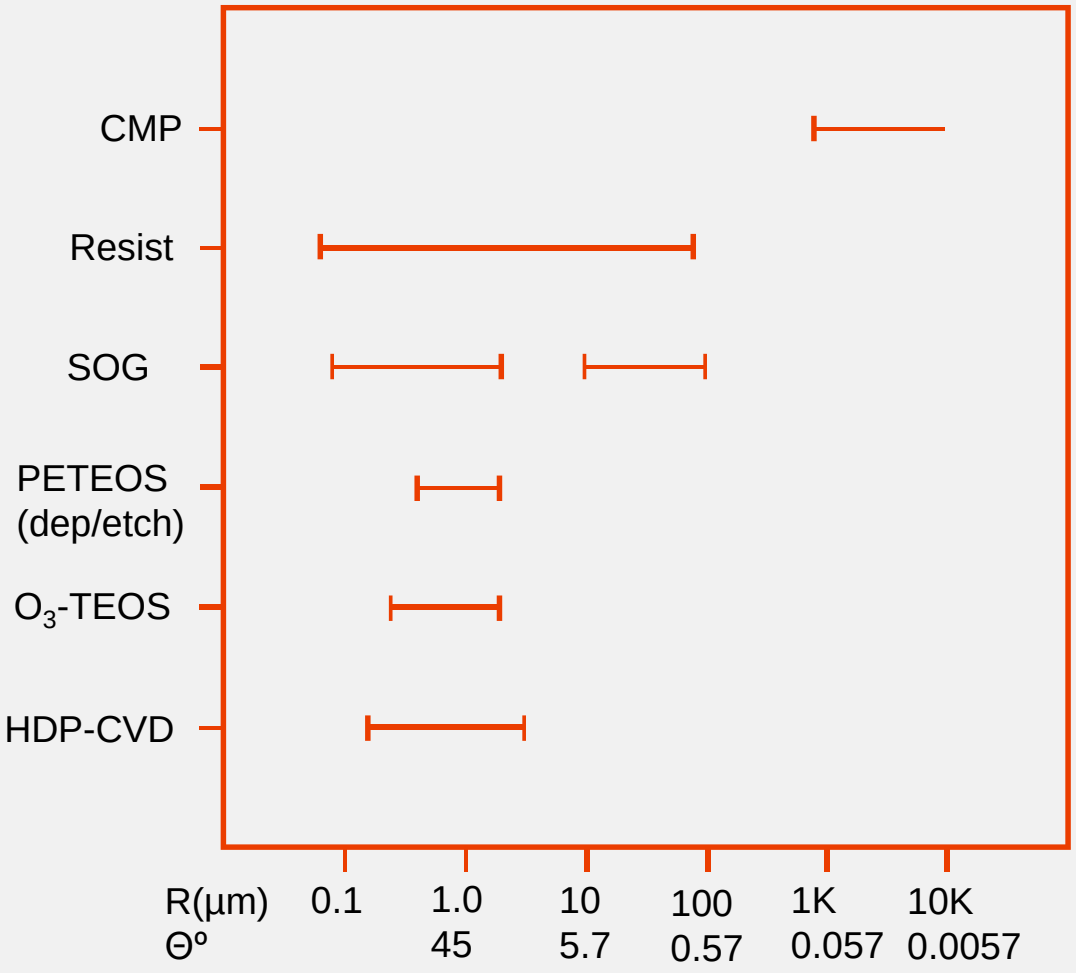
e.g. Copper 400 nm/min Oxide 40 nm/min ➔ 10:1
e.g. Copper 400 nm/min TaN 10 nm/min ➔ 40:1

Polish stop: if selectivity is very high, we call it polish stop (even though some underlying material is removed)

Planarization



R – planarization length



TEOS - Tetraethyl orthosilicate, 600C

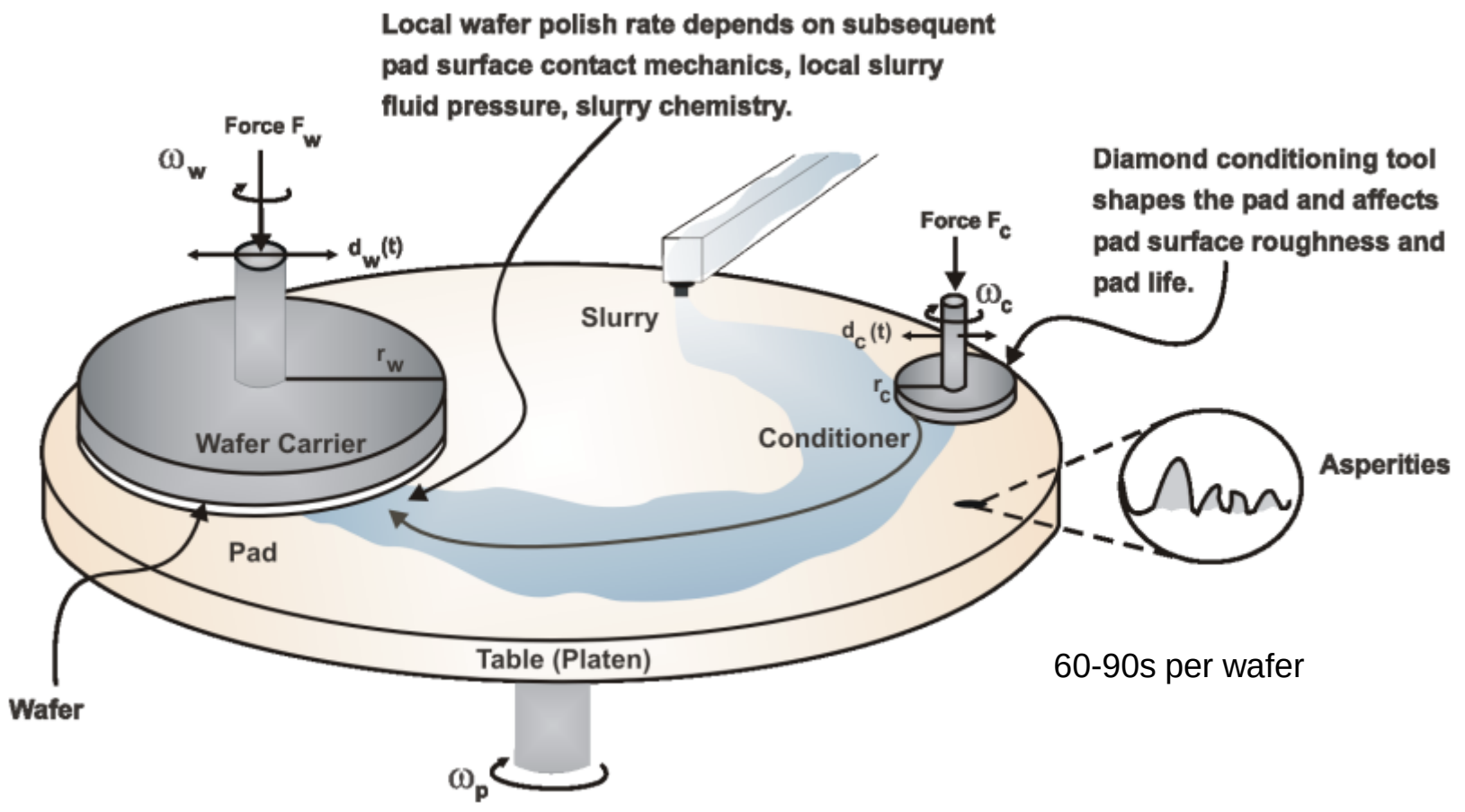
PETEOS – plasma enhanced TEOS, 400C

O_3-TEOS – TEOS plus O_3 CVD, 400C

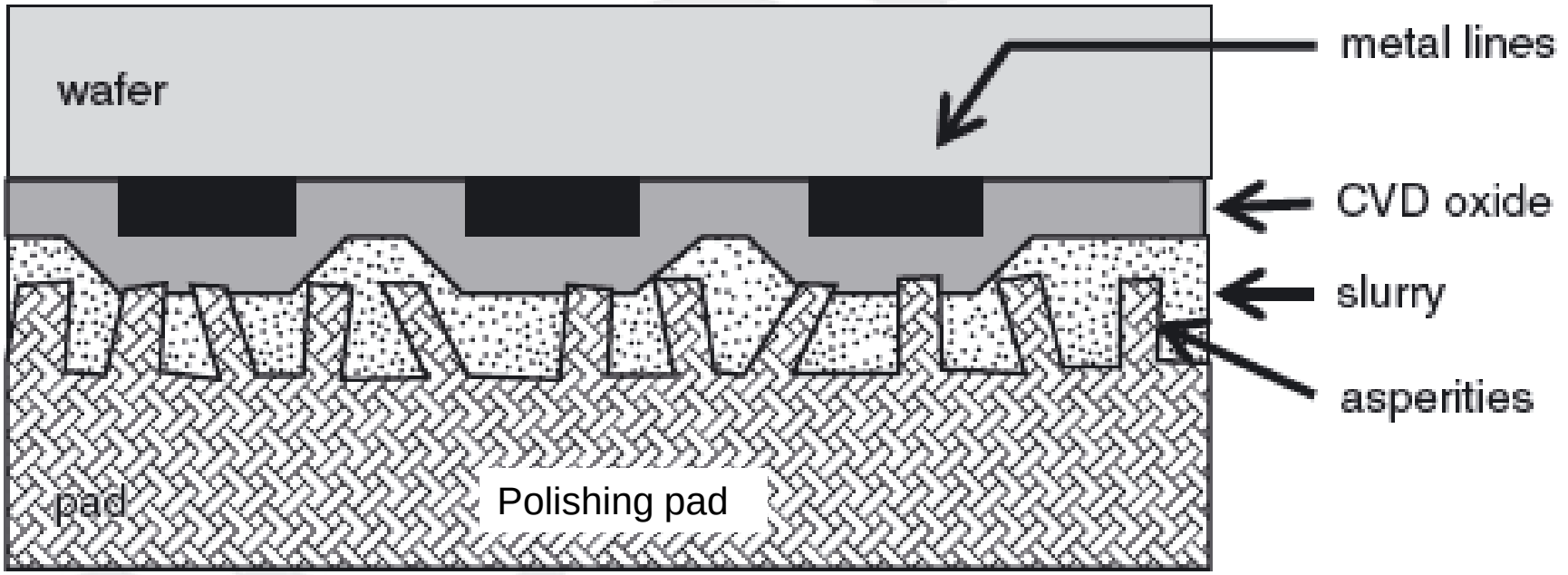
SOG – spin on glass

HDP-CVD – high density plasma CVD, 100C

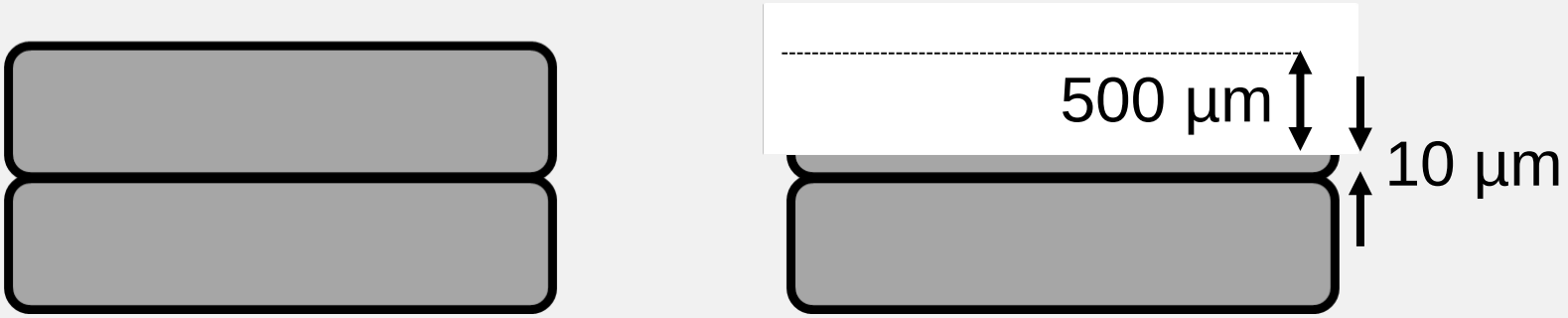
Rotary CMP tool



Polishing in action



Grinding vs. polishing

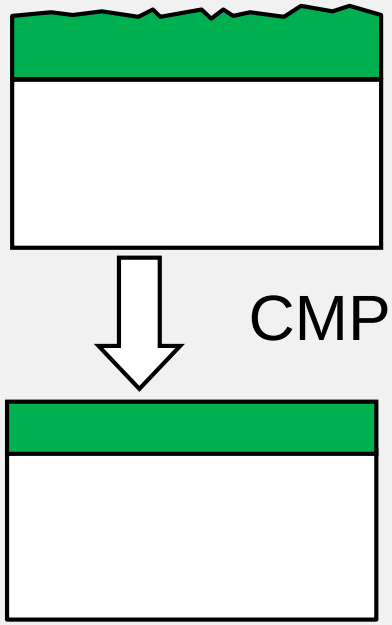


Both use abrasive particles, but:

Grinding removes 10 µm/min in large chunks because large particles
Grinding results in very rough surface because very large chunks
Grinding leaves mechanical damage due to large chunks being torn off

Polishing uses nanoparticles to achieve smooth surfaces
Polishing removes 0.1 µm/min because small particles, small forces
Mechanism of removal is chemical and mechanical (CMP !)

Polishing needed after grinding !

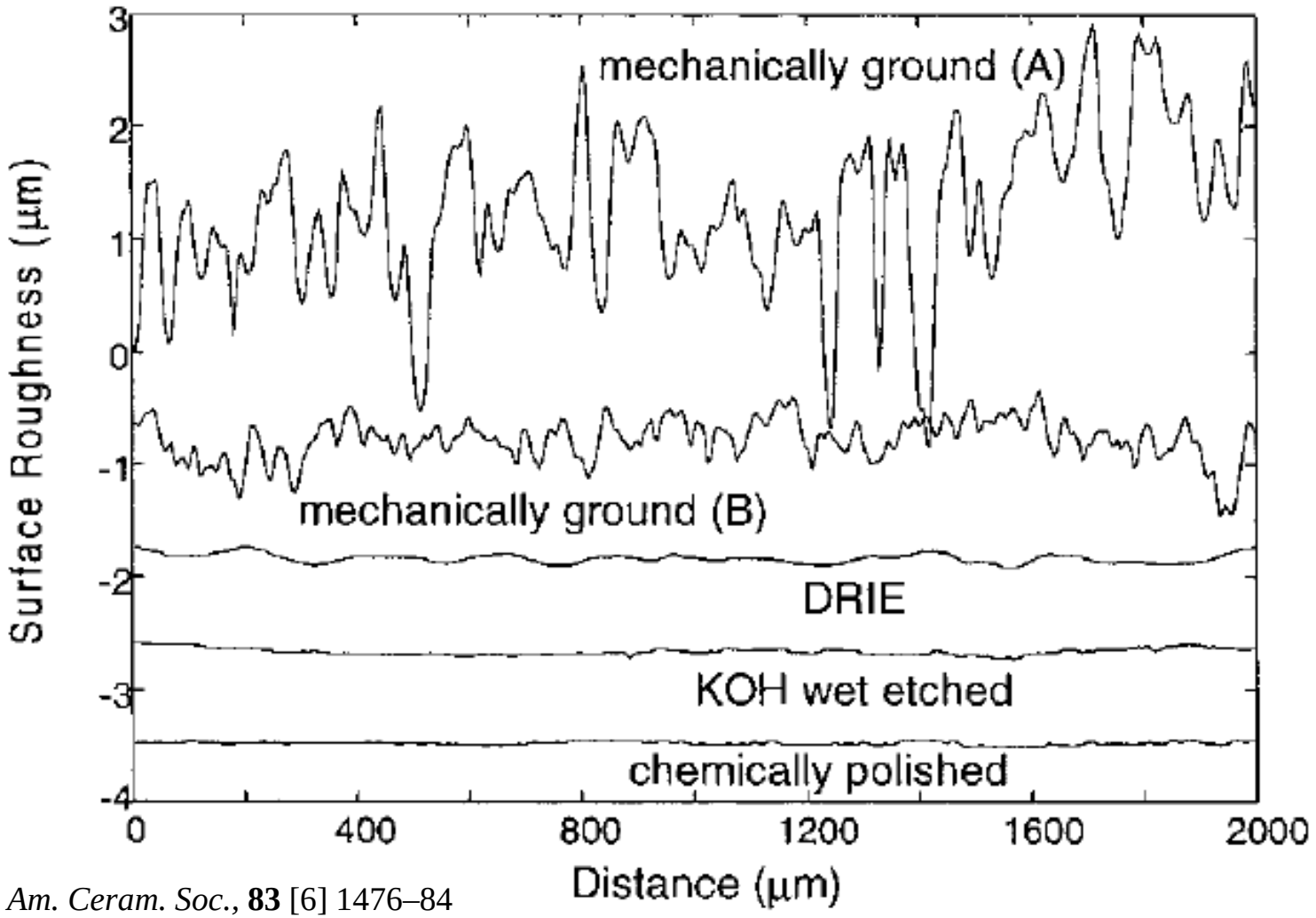


Surface roughness e.g. 200 nm

Surface roughness e.g. 1 nm

Surface roughness

Log scale



J. Am. Ceram. Soc., **83** [6] 1476–84

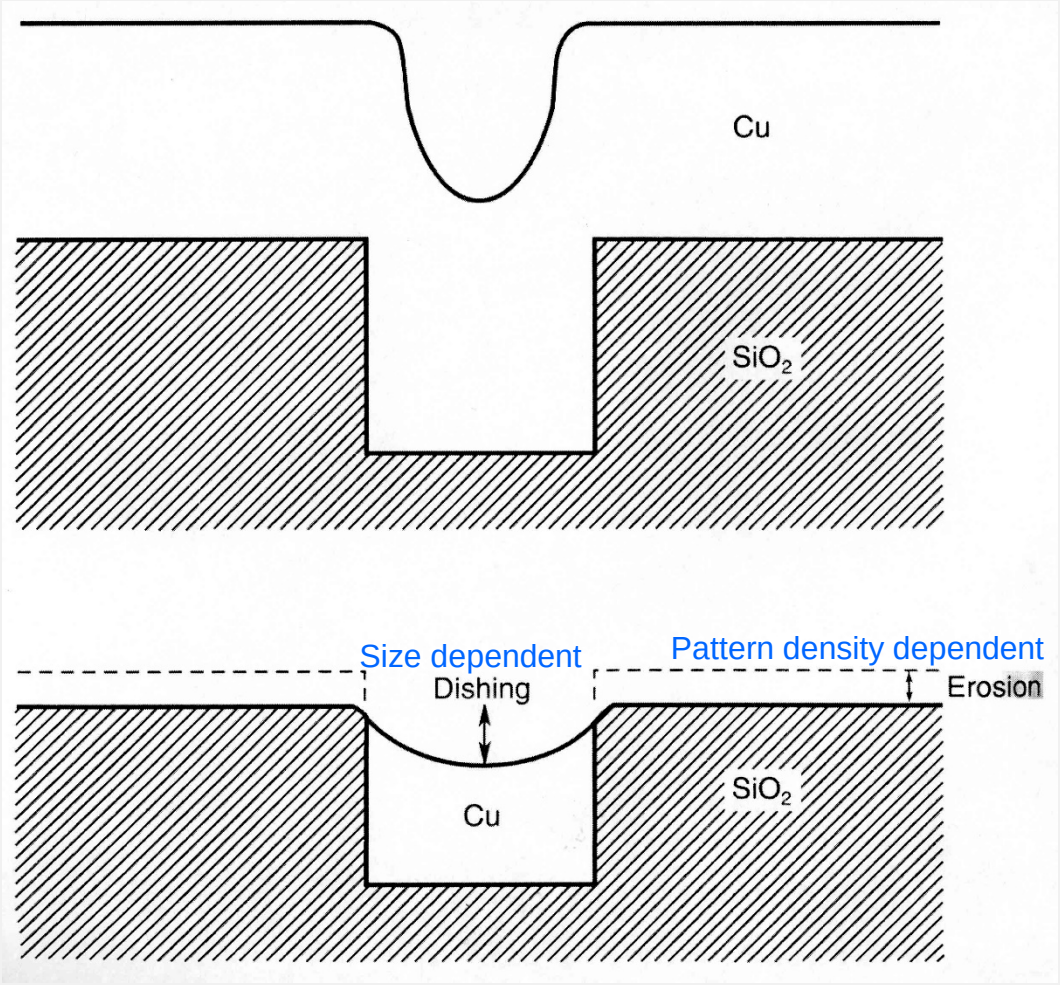
CMP tool input variables

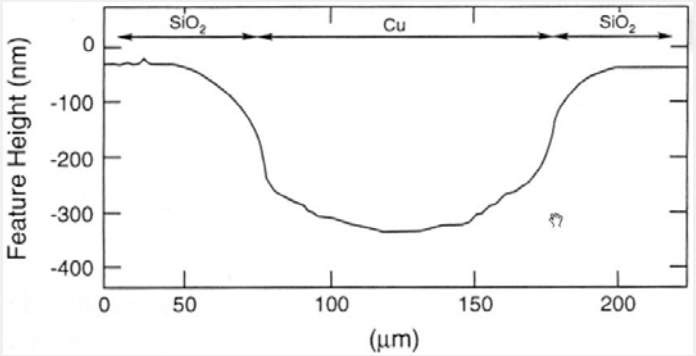
- -platen rotation 10-100 rpm
- -velocity 10-100 cm/s
- -applied pressure (load) 10-50 kPa
- -slurry supply rate 50-500 ml/min
- -slurry chemicals (pH, conc., viscosity,...)
- -pad (material, porosity, hardness,...)
- -abrasives (size,type, hardness, conc.,...)
- -wafer (curvature, mounting, backpressure)
- -patterns (size, density, ...)
- -films (hardness, μ-structure, stress, ...)

Process outputs resemble etching ones

- -polish rate, 100-500 nm/min
- -selectivity 1:1 – 100:1
  (blind polishing and stopped polishing)
- -overpolish time
- -pattern density effects
- -uniformity across wafer, 10%
- -wafer-to-wafer repeatability, 10%

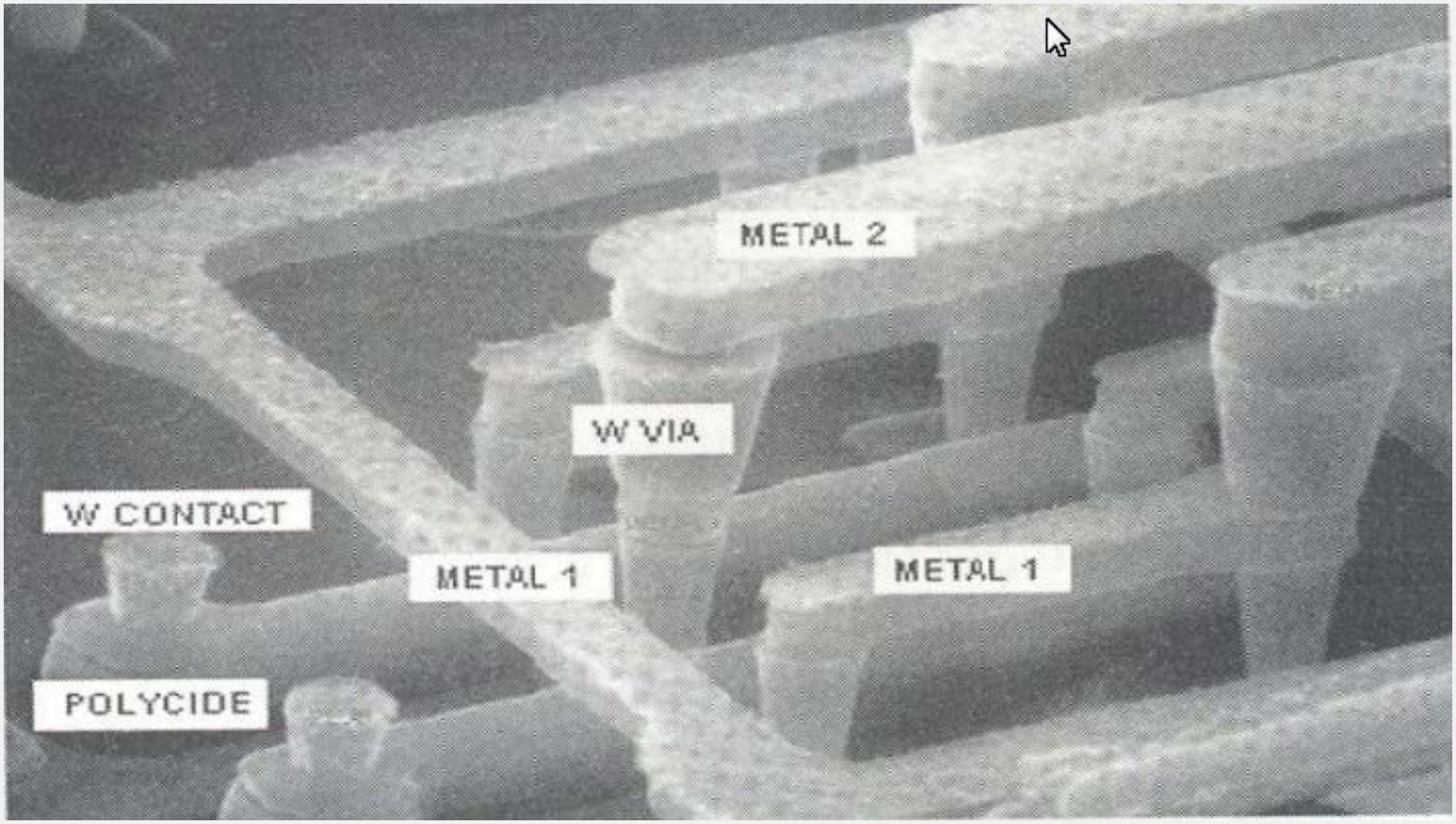
Erosion and dishing in CMP





Plug recess – pure chemical etching of metal

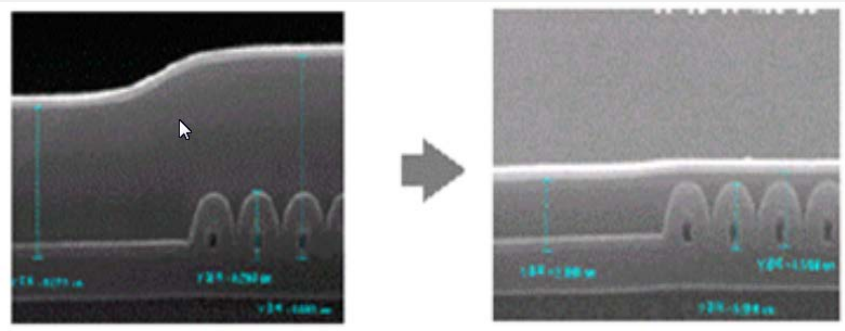
Planarization in multilevel metallization



Silicon VLSI Technology by Plummer et al.

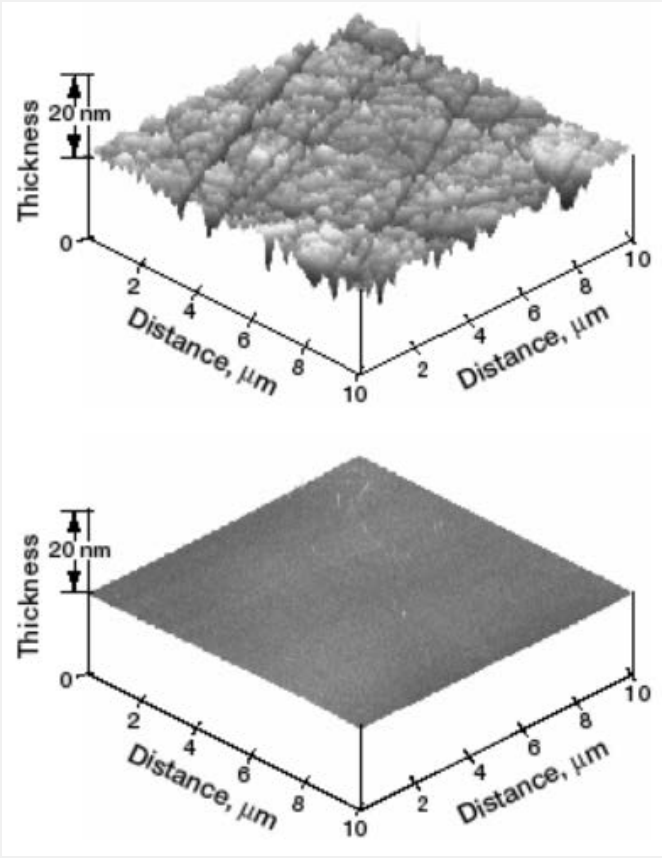
Results of CMP

CMP of SiO_2



Planarization

SiC wafer before and after CMP



Etching and CMP

- The same rate 100 – 1000 nm/min
- Surface/transport limitation of reactions
- Pattern dependency is the same, but pattern size effect is opposite
- Chemical and physical effects – ions in RIE and mechanical force in CMP
- Preferred directions/planes – verticlal in RIE and horizontal in CMP
- Post-CMP cleaning is more chanllenging than post-etching one